

ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9

TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43

e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT808150GO TECHNICAL DATA

High Power Infrared Laserdiode

Emitting Dimensions: **100 x 1 μm**

Lasing wavelength: **808 nm typ.**

Max. optical power: **150 mW**

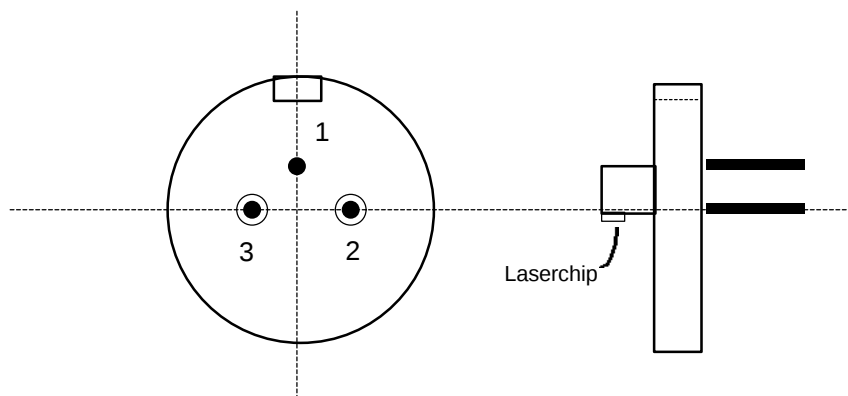
Package: **9 mm open package**



NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:

- 1: laserdiode anode
- 2: N.C.
- 3: laserdiode cathode



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	200	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
Operating Case Temperature	T_c	-20 .. +50	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 .. +80	$^\circ\text{C}$

Optical-Electrical Characteristics ($T_c = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	cw		150		mW
Operation Current	I_{op}	$P_o = 150 \text{ mW}$		0.4		A
Operation Voltage	V_{op}	$P_o = 150 \text{ mW}$		2.4		V
Lasing Wavelength	λ_p	$P_o = 150 \text{ mW}$	805	808	811	nm
Beam Divergence	θ	$P_o = 150 \text{ mW}$		10x30		$^\circ$